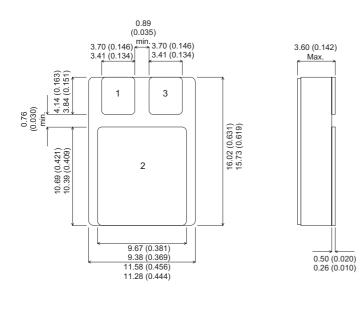
2N3741 SMD



MECHANICAL DATA

Dimensions in mm



SMD1

MEDIUM POWER PNP SILICON POWER TRANSISTOR

- •LOW SATURATION VOLTAGE
- HIGH GAIN

FEATURES

- Hermetically sealed Surface Mount Package.
- Small Footprint efficient use of PCB space.
- Lightweight
- High Packing Densities

Complementary to NPN 2N3766SMD

Pad 1 – Base

Pad 2 - Collector Pad 3 - Emitter

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C unless otherwise stated)

V _{CBO}	Collector – Base Voltage	80V		
V _{CEO}	Collector – Emitter Voltage ($I_B = 0$) 80V			
V_{EBO}	Emitter – Base Voltage ($I_{C} = 0$)	7V		
I _C	Collector Current	4A		
I _{C(PK)}	Peak Collector Current	10A		
I _B	Base Current	2A		
P _{tot}	Total Dissipation at $T_{case} = 25^{\circ}C$	50W		
T _{stg}	Operating and Storage Temperature Range	–65 to 200°C		

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.





ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

	Parameter	Test Cond	itions	Min.	Тур.	Max.	Unit			
	ELECTRICAL CHARACTERISTICS									
V _{CEO(sus)*}	Collector – Emitter Sustaining Voltage	I _C = 100mA	I _B = 0	80			V			
I _{CBO}	Collector Base Cut–Off Current	V _{CB} = 80V	I _E = 0			100	μΑ			
I _{CEO}	Collector Emiiter Cut–Off Current	$V_{CE} = 60V$	I _B = 0			1.0	mA			
I _{CEX}	Collector Cut–Off Current	V _{CE} = 80V	$V_{BE(OFF)} = 1.5V$			100	μΑ			
		V _{CE} = 60V	$V_{BE(OFF)} = 1.5V$			1	mA			
			$T_{\rm C} = 150^{\circ}{\rm C}$							
I _{EBO}	Emitter Base Cut–Off Current	$V_{EB} = 7V$				0.5	mA			
h _{FE*}	DC Current Gain	I _C = 100mA	$V_{CE} = 1V$	40						
		I _C = 250mA	$V_{CE} = 1V$	30		100				
		I _C = 500mA	$V_{CE} = 1V$	20						
		I _C = 1A	$V_{CE} = 1V$	10						
V _{CE(sat)*}	Collector - Emitter Saturation Voltage	I _C = 1A	I _B = 125mA			0.6	V			
V _{BE*}	Base – Emitter Saturation Voltage	I _C = 250mA	$I_B = 1V$			1.0				
	DYNAMIC CHARACTERISTICS	1	I							
f _t	Transition Frequency	I _C = 100mA	$V_{CE} = 10V$	3			MHz			
			f = 1MHz	4						
C _{ob}	Output Capacitance	V _{CB} = 10V	I _C = 0		100					
			f = 100KHz			100	pF			
h _{fe}	Small Signal Current Gain	I _C = 50mA	V _{CE} = 10V	25						
			f = 1KHz				-			

* Pulse Width $\leq 300 \mu s$, Duty Cycle < 2%

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